

BCR5PM-12L

Triac

Medium Power Use

(The product guaranteed maximum junction temperature of 150°C)

REJ03G0460-0300 Rev.3.00 Mar 06, 2007

Features

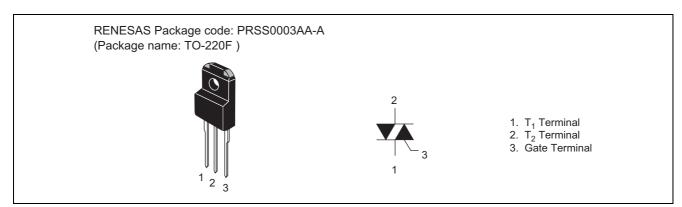
I_{T (RMS)}: 5 A
 V_{DRM}: 600 V

• I_{FGTI} , I_{RGTI} , I_{RGTIII} : 20 mA (10 mA)^{Note5}

Viso: 2000 VInsulated Type

• Planar Passivation Type

Outline



Applications

Switching mode power supply, light dimmer, electronic flasher unit, control of household equipment such as TV sets, stereo systems, refrigerator, washing machine, infrared kotatsu, carpet, solenoid driver, small motor control, copying machine, electric tool, electric heater control, and other general controlling device

Warning

- 1. Refer to the recommended circuit values around the triac before using.
- 2. Be sure to exchange the specification before using. Otherwise, general triacs with the maximum junction temperature of 125°C will be supplied.

Maximum Ratings

Parameter	Symbol	Voltage class	Unit		
Faianetei	Symbol	12	Offic		
Repetitive peak off-state voltage ^{Note1}	V_{DRM}	600	V		
Non-repetitive peak off-state voltage ^{Note1}	V_{DSM}	720	V		

BCR5PM-12L (The product guaranteed maximum junction temperature of 150°C)

Parameter	Symbol	Ratings	Unit	Conditions
RMS on-state current	I _{T (RMS)}	5	Α	Commercial frequency, sine full wave
				360° conduction, Tc = 120°C
Surge on-state current	I _{TSM}	50	Α	60Hz sinewave 1 full cycle, peak value,
				non-repetitive
I ² t for fusing	l ² t	10.4	A ² s	Value corresponding to 1 cycle of half
				wave 60Hz, surge on-state current
Peak gate power dissipation	P_{GM}	3	W	
Average gate power dissipation	P _{G (AV)}	0.3	W	
Peak gate voltage	V_{GM}	10	V	
Peak gate current	I _{GM}	2	Α	
Junction temperature	Tj	- 40 to +150	°C	
Storage temperature	Tstg	- 40 to +150	°C	
Mass	_	2.0	g	Typical value
Isolation voltage	Viso	2000	V	Ta = 25°C, AC 1 minute,
				T ₁ ·T ₂ ·G terminal to case

Notes: 1. Gate open.

Electrical Characteristics

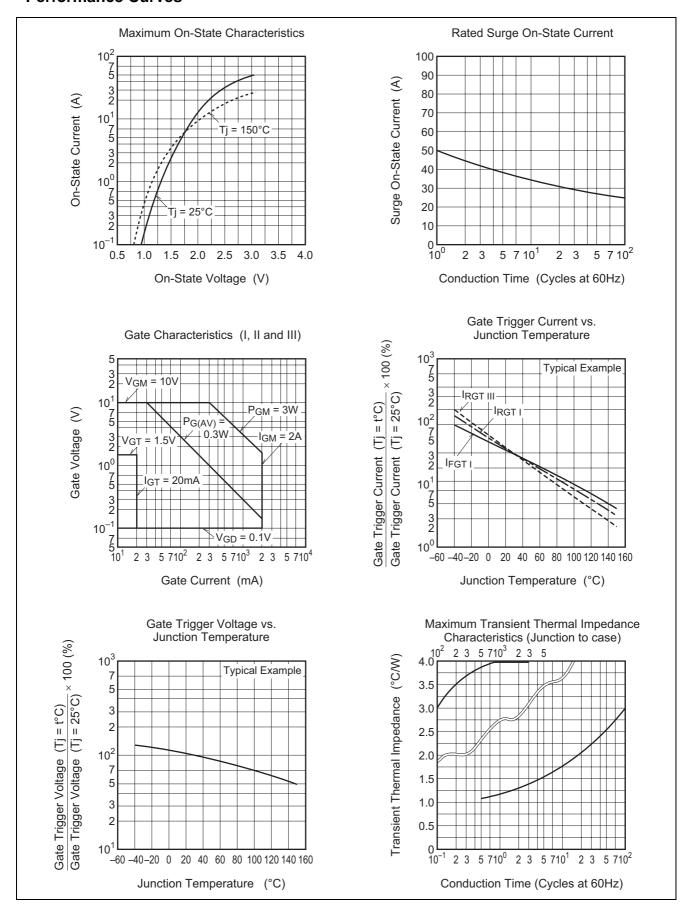
Parameter		Symbol	Min.	Тур.	Max.	Unit	Test conditions
Repetitive peak off-state current		I _{DRM}	_	_	2.0	mA	Tj = 150°C, V _{DRM} applied
On-state voltage		V_{TM}	_	_	1.8	V	Tc = 25°C, I _{TM} = 7 A, Instantaneous measurement
Gate trigger voltage ^{Note2}	I	V_{FGTI}	_	_	1.5	٧	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	V_{RGTI}	_	_	1.5	V	$R_G = 330 \Omega$
	III	V_{RGTIII}	_	_	1.5	V	
Gate trigger current ^{Note2}	I	I_{FGTI}	_	_	20 ^{Note5}	mA	$Tj = 25$ °C, $V_D = 6$ V, $R_L = 6$ Ω,
	II	$I_{RGT_{I}}$	_	_	20 ^{Note5}	mA	$R_G = 330 \Omega$
	III	$I_{RGT_{III}}$	_	_	20 ^{Note5}	mA	
Gate non-trigger voltage		V_{GD}	0.2/0.1	_	_	V	$Tj = 125^{\circ}C/150^{\circ}C, V_D = 1/2 V_{DRM}$
Thermal resistance		R _{th (j-c)}	_	_	4.0	°C/W	Junction to case ^{Note3}
Critical-rate of rise of off-state commutating voltage ^{Note4}		(dv/dt)c	5/1	_	_	V/μs	Tj = 125°C/150°C

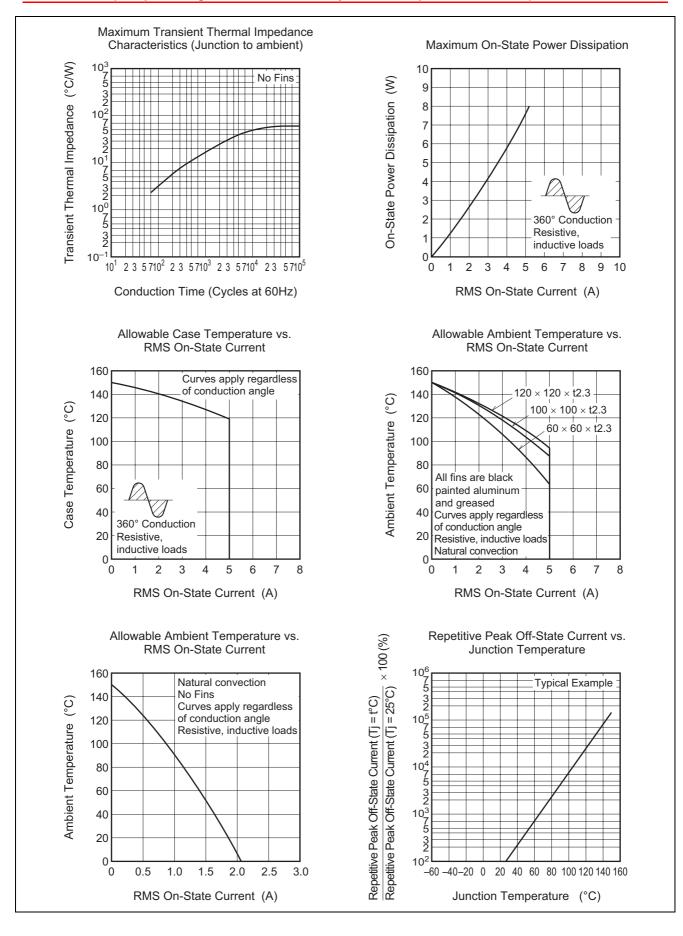
Notes: 2. Measurement using the gate trigger characteristics measurement circuit.

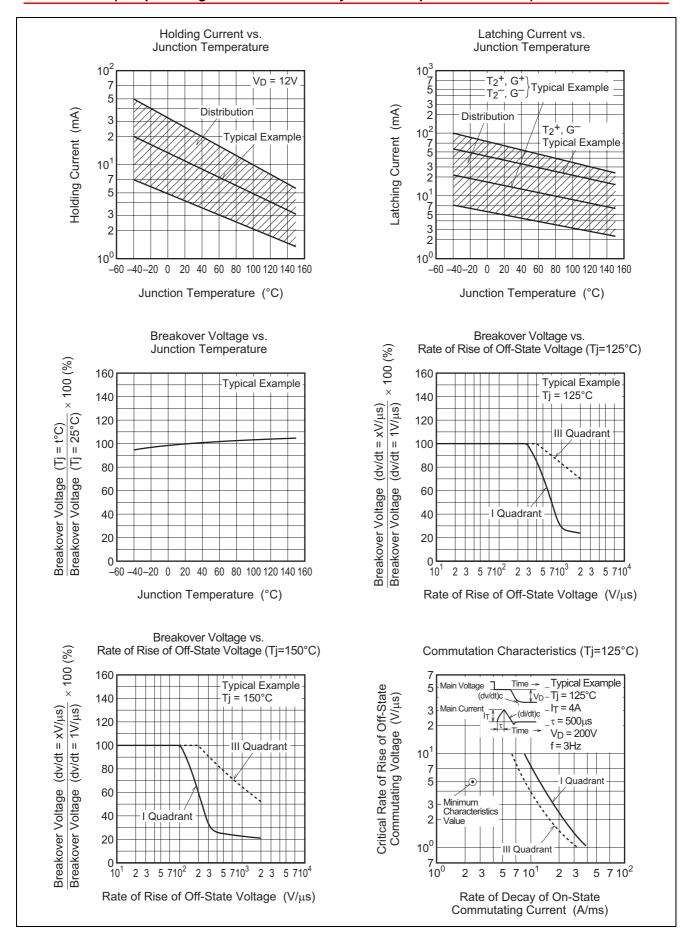
- 3. The contact thermal resistance $R_{th\ (c-f)}$ in case of greasing is $0.5^{\circ}C/W$.
- 4. Test conditions of the critical-rate of rise of off-state commutating voltage is shown in the table below.
- 5. High sensitivity ($I_{GT} \le 10$ mA) is also available. (I_{GT} item: 1)

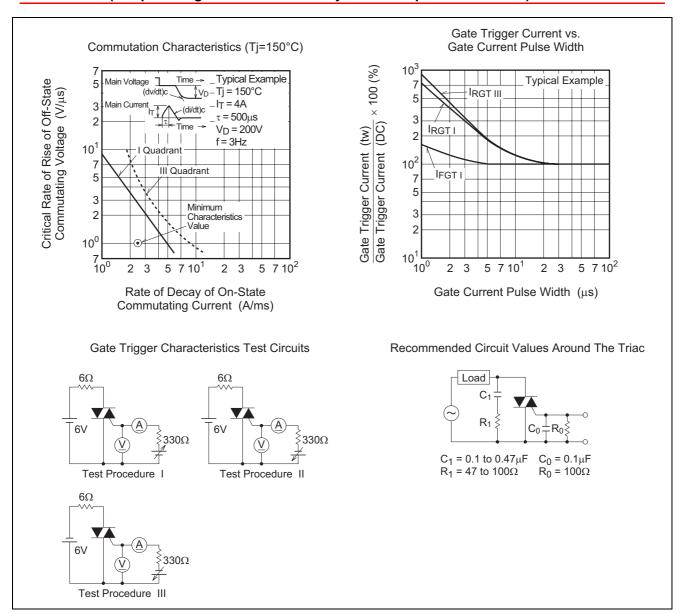
Test conditions	Commutating voltage and current waveforms (inductive load)		
1. Junction temperature Tj = 125°C/150°C	Supply Voltage → Time		
2. Rate of decay of on-state commutating current (di/dt)c = - 2.5 A/ms	Main Current (di/dt)c → Time		
3. Peak off-state voltage $V_D = 400 \text{ V}$	Main Voltage Time		

Performance Curves

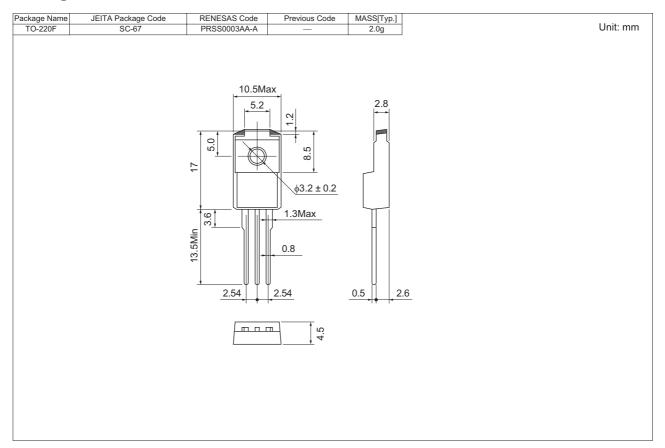








Package Dimensions



Order Code

Lead form	Standard packing	Quantity	Standard order code	Standard order code example
Straight type	Vinyl sack	100	Type name +B	BCR5PM-12LB
Lead form	Plastic Magazine (Tube)	50	Type name +B – Lead forming code	BCR5PM-12LB-A8

Note: Please confirm the specification about the shipping in detail.

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